



TLV313-Q1 低消費電力、レール・ツー・レール入出力、 オフセット標準値750 μ V、低コスト・システム用の1MHzオペアンプ

1 特長

- 車載アプリケーションに対応
- 下記内容でAEC-Q100認定済み
 - デバイス温度グレード1: 動作時周囲温度範囲
–40°C ~ +125°C
 - デバイスHBM ESD分類レベル3A
 - デバイスCDM ESD分類レベルC6
- 低コストのシステム用の高精度アンプ
- 低い I_Q : 65 μ A/ch
- 広い電源電圧範囲: 1.8V ~ 5.5V
- 低ノイズ: 1kHz時に26nV/ $\sqrt{\text{Hz}}$
- ゲイン帯域幅: 1MHz
- レール・ツー・レール入出力
- 低い入力バイアス電流: 1pA
- 低いオフセット電圧: 0.75mV
- ユニティ・ゲインで安定
- 内部RFI/EMIフィルタ

2 アプリケーション

- インフォテインメント
- エンジン制御ユニット
- 車載照明
- ローサイド・センシング
- バッテリー管理システム
- パッシブ型安全運転支援システム
- 静電容量式センシング
- 燃料ポンプ

3 概要

TLVx313-Q1ファミリのシングルおよびデュアル・チャネルのオペアンプは、低消費電力と優れた性能を両立した製品です。このため、インフォテインメント、エンジン制御ユニット、車載照明などの広範なアプリケーションに適しています。このファミリはレール・ツー・レール入出力(RRIO)、低い静止電流(標準値65 μ A)、広い帯域幅(1MHz)、非常に低いノイズ(1kHzにおいて26nV/ $\sqrt{\text{Hz}}$)という特長があるため、コストと性能の適切なバランスが必要な各種のバッテリー駆動アプリケーションに最適です。さらに、入力バイアス電流が小さいため、これらのデバイスはソース・インピーダンスがメガオーム単位のアプリケーションでも使用できます。

TLVx313-Q1デバイスは堅牢に設計されており、100pFまでの容量性負荷に対するユニティ・ゲイン安定性、RFI/EMI除去フィルタの搭載、オーバードライブ状態で位相反転が発生しない、高い静電放電(ESD)保護(4kV HBM)といった特長があるため、回路設計が容易です。

これらのデバイスは、1.8V (± 0.9 V) ~ 5.5V (± 2.75 V)の電圧で動作するよう最適化され、拡張温度範囲の-40°C ~ +125°Cでの動作が規定されています。

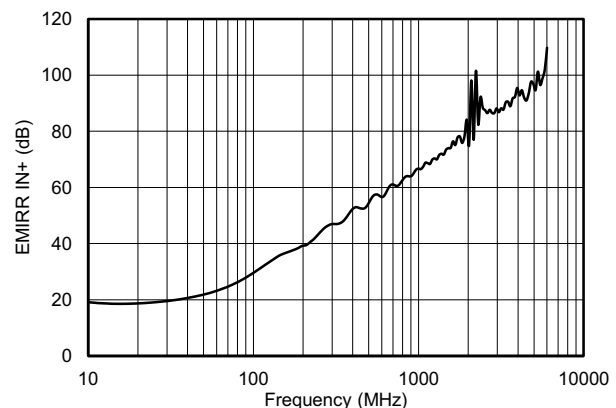
シングル・チャネルのTLV313-Q1デバイスはSC70-5パッケージで供給され、デュアル・チャネルのTLV2313-Q1デバイスはSOIC-8 (D)およびVSSOP-8 (DGK)パッケージで供給されます。

製品情報⁽¹⁾

型番	パッケージ	本体サイズ(公称)
TLV313-Q1	SC70 (5)	2.00mm×1.25mm
TLV2313-Q1	SOIC (8)	4.90mm×3.91mm
	VSSOP (8)	3.00mm×3.00mm

(1) 提供されているすべてのパッケージについては、データシートの末尾にある注文情報を参照してください。

EMIRR IN+と周波数との関係



目次

1	特長	1	8.4	Device Functional Modes.....	15
2	アプリケーション	1	9	Application and Implementation	16
3	概要	1	9.1	Application Information.....	16
4	改訂履歴	2	9.2	Typical Application	16
5	Device Comparison Table	3	9.3	System Examples	17
6	Pin Configuration and Functions	3	10	Power Supply Recommendations	18
7	Specifications	5	11	Layout	19
7.1	Absolute Maximum Ratings	5	11.1	Layout Guidelines	19
7.2	ESD Ratings.....	5	11.2	Layout Example: Single Channel.....	19
7.3	Recommended Operating Conditions.....	5	11.3	Layout Example: Dual Channel	20
7.4	Thermal Information: TLV313-Q1	6	12	デバイスおよびドキュメントのサポート	21
7.5	Thermal Information: TLV2313-Q1	6	12.1	ドキュメントのサポート	21
7.6	Electrical Characteristics: 5.5 V	7	12.2	関連リンク	21
7.7	Electrical Characteristics: 1.8 V	8	12.3	ドキュメントの更新通知を受け取る方法.....	21
7.8	Typical Characteristics: Table of Graphs	9	12.4	コミュニティ・リソース	21
7.9	Typical Characteristics.....	10	12.5	商標	21
8	Detailed Description	13	12.6	静電気放電に関する注意事項	21
8.1	Overview	13	12.7	Glossary	21
8.2	Functional Block Diagram	13	13	メカニカル、パッケージ、および注文情報	21
8.3	Feature Description.....	14			

4 改訂履歴

2017年10月発行のものから更新

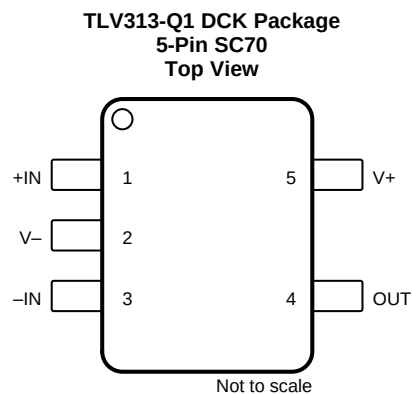
Page

•	TLV2313-Q1デバイスをデータシートに追加.....	1
•	データシート全体を通してTLV2313-Q1デバイスのデュアル・チャネルの情報を追加	1
•	変更 <i>Input and ESD Protection</i> section From <i>Power Supply</i> section : To <i>Feature Description</i> section.....	15
•	変更「関連資料」セクションのフォーマット	21

5 Device Comparison Table

DEVICE	NO. OF CHANNELS	PACKAGE LEADS		
		SC70 (DCK)	SOIC (D)	VSSOP (DGK)
TLV313-Q1	1	5	—	—
TLV2313-Q1	2	—	8	8

6 Pin Configuration and Functions



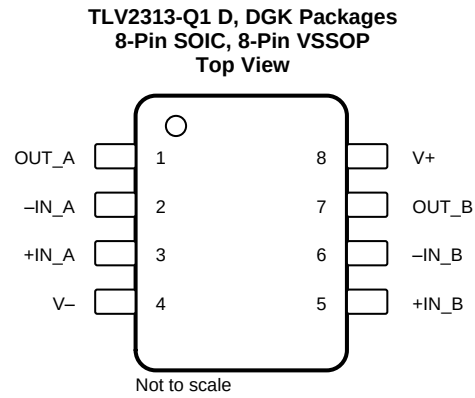
Pin Functions: TLV313-Q1

PIN		I/O	DESCRIPTION
NAME	NO.		
+IN	1	I	Noninverting input
–IN	3	I	Inverting input
OUT	4	O	Output
V–	2	—	Negative (lowest) power supply
V+	5	—	Positive (highest) power supply

TLV313-Q1, TLV2313-Q1

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Pin Functions: TLV2313-Q1

NAME	PIN		I/O	DESCRIPTION
	D (SOIC)	DGK (VSSOP)		
V–	4	4	—	Negative (lowest) power supply
V+	8	8	—	Positive (highest) power supply
OUT A	1	1	O	Output, channel A
OUT B	7	7	O	Output, channel B
–IN A	2	2	I	Inverting input, channel A
+IN A	3	3	I	Noninverting input, channel A
–IN B	6	6	I	Inverting input, channel B
+IN B	5	5	I	Noninverting input, channel B

7 Specifications

7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
Voltage	Supply voltage (V+) – (V–)	0	7	V
	Signal input terminals ⁽²⁾	(V–) – (0.5)	(V+) + 0.5	
Current	Signal input terminals ⁽²⁾	–10	10	mA
	Output short circuit ⁽³⁾	Continuous		
Temperature	Operating, T _A	–40	150	°C
	Junction, T _J		150	
	Storage, T _{stg}	–65	150	

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) Input pins are diode-clamped to the power-supply rails. Input signals that may swing more than 0.5 V beyond the supply rails must be current limited to 10 mA or less.
- (3) Short-circuit to ground, one amplifier per package.

7.2 ESD Ratings

		VALUE	UNIT
V _(ESD) Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±4000	V
	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1000	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V _S	Supply voltage	1.8	5.5	V
T _A	Specified temperature	–40	125	°C

TLV313-Q1, TLV2313-Q1

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7.4 Thermal Information: TLV313-Q1

THERMAL METRIC ⁽¹⁾		TLV313-Q1	UNIT
		DCK (SC70)	
		5 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	281.4	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	91.6	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	59.6	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	1.5	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	58.8	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

7.5 Thermal Information: TLV2313-Q1

THERMAL METRIC		TLV2313-Q1		UNIT
		D (SOIC)	DGK (VSSOP)	
		8 PINS	8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	131.6	186.0	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	71.4	73.2	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	75.4	107.3	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	22.7	14.4	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	74.6	105.6	°C/W

7.6 Electrical Characteristics: 5.5 V

at $T_A = 25^\circ\text{C}$, $R_L = 10\text{ k}\Omega$ connected to $V_S / 2$, and $V_{CM} = V_{OUT} = V_S / 2$, (unless otherwise noted)⁽¹⁾

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFFSET VOLTAGE						
V _{OS}	Input offset voltage			0.75	3	mV
dV _{OS} /dT	Input offset voltage vs temperature	T _A = −40°C to 125°C		2		μV/°C
PSRR	Power-supply rejection ratio		74	90		dB
INPUT VOLTAGE RANGE						
V _{CM}	Common-mode voltage range	No phase reversal, rail-to-rail input	(V−) − 0.2		(V+) + 0.2	V
CMRR	Common-mode rejection ratio	(V−) − 0.2 V < V _{CM} < (V+) − 1.3 V		85		dB
		V _{CM} = −0.2 V to 5.7 V	64	80		
INPUT BIAS CURRENT						
I _B	Input bias current			±1		pA
I _{OS}	Input offset current			±1		pA
NOISE						
	Input voltage noise (peak-to-peak)	f = 0.1 Hz to 10 Hz		6		μV _{PP}
e _n	Input voltage noise density	f = 10 kHz		22		nV/√Hz
		f = 1 kHz		26		
i _n	Input current noise density	f = 1 kHz		5		fA/√Hz
INPUT CAPACITANCE						
C _{IN}	Differential			1		pF
	Common-mode			5		
OPEN-LOOP GAIN						
A _{OL}	Open-loop voltage gain	0.05 V < V _O < (V+) − 0.05 V R _L = 100 kΩ		104		dB
		0.3 V < V _O < (V+) − 0.3 V R _L = 2 kΩ	100	110		
	Phase margin	V _S = 5 V, G = +1		65		°
FREQUENCY RESPONSE						
GBW	Gain-bandwidth product	V _S = 5 V, C _L = 10 pF		1		MHz
SR	Slew rate	V _S = 5 V, G = +1		0.5		V/μs
t _S	Settling time	To 0.01%, V _S = 5 V, 2-V step , G = +1		6		μs
	Overload recovery time	V _S = 5 V, V _{IN} × Gain > V _S		3		μs
OUTPUT						
V _O	Voltage output swing from supply rails	R _L = 100 kΩ ⁽²⁾		5	20	mV
		R _L = 2 kΩ ⁽²⁾		75	100	
I _{SC}	Short-circuit current			±15		mA
R _O	Open-loop output impedance			2300		Ω
POWER SUPPLY						
V _S	Specified voltage range		1.8 (±0.9)	5.5 (±2.75)		V
I _Q	Quiescent current per amplifier	T _A = −40°C to 125°C, V _S = 5 V, I _O = 0 mA		65	90	μA
	Power-on time	V _S = 0 V to 5 V, to 90% I _O level		10		μs

(1) Parameters with minimum or maximum specification limits are 100% production tested at 25°C , unless otherwise noted. Over-temperature limits are based on characterization and statistical analysis.

(2) Specified by design and characterization; not production tested.

TLV313-Q1, TLV2313-Q1

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7.7 Electrical Characteristics: 1.8 V

 at $T_A = 25^\circ\text{C}$, $R_L = 10\text{ k}\Omega$ connected to $V_S / 2$, $V_{CM} = V_{S+} - 1.3\text{ V}$, and $V_{OUT} = V_S / 2$, (unless otherwise noted)⁽¹⁾

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFFSET VOLTAGE						
V _{OS}	Input offset voltage			0.75	3	mV
dV _{OS} /dT	Input offset voltage vs temperature	T _A = −40°C to 125°C		2		μV/°C
PSRR	Power-supply rejection ratio		74	90		dB
INPUT VOLTAGE RANGE						
V _{CM}	Common-mode voltage range	No phase reversal, rail-to-rail input	(V−) − 0.2		(V+) + 0.2	V
CMRR	Common-mode rejection ratio	(V _{S−}) − 0.2 V < V _{CM} < (V _{S+}) − 1.3 V		85		dB
		V _{CM} = −0.2 V to 1.8 V		73		
INPUT BIAS CURRENT						
I _B	Input bias current			±1		pA
I _{OS}	Input offset current			±1		pA
NOISE						
	Input voltage noise (peak-to-peak)	f = 0.1 Hz to 10 Hz		6		μV _{PP}
e _n	Input voltage noise density	f = 10 kHz		22		nV/√Hz
		f = 1 kHz		26		
i _n	Input current noise density	f = 1 kHz		5		fA/√Hz
INPUT CAPACITANCE						
C _{IN}	Differential			1		pF
	Common-mode			5		
OPEN-LOOP GAIN						
A _{OL}	Open-loop voltage gain	0.1 V < V _O < (V+) − 0.1 V, R _L = 10 kΩ		110		dB
		0.05 V < V _O < (V+) − 0.05 V, R _L = 100 kΩ		110		
FREQUENCY RESPONSE						
GBW	Gain-bandwidth product	C _L = 10 pF		0.9		MHz
SR	Slew rate	G = 1		0.45		V/μs
OUTPUT						
V _O	Voltage output swing from supply rails	R _L = 100 kΩ ⁽²⁾		5		mV
		R _L = 2 kΩ ⁽²⁾		25		
I _{SC}	Short-circuit current			±6		mA
R _O	Open-loop output impedance			2300		Ω

 (1) Parameters with minimum or maximum specification limits are 100% production tested at 25°C , unless otherwise noted. Over-temperature limits are based on characterization and statistical analysis.

(2) Specified by design and characterization; not production tested.

7.8 Typical Characteristics: Table of Graphs

表 1. Table of Graphs

TITLE	FIGURE
Open-Loop Gain and Phase vs Frequency	Figure 1
Quiescent Current vs Supply Voltage	Figure 2
Offset Voltage Production Distribution	Figure 3
Offset Voltage vs Common-Mode Voltage (Maximum Supply)	Figure 4
CMRR and PSRR vs Frequency (RTI)	Figure 5
0.1-Hz to 10-Hz Input Voltage Noise (5.5 V)	Figure 6
Input Voltage Noise Spectral Density vs Frequency (1.8 V, 5.5 V)	Figure 7
Input Bias and Offset Current vs Temperature	Figure 8
Open-Loop Output Impedance vs Frequency	Figure 9
Maximum Output Voltage vs Frequency and Supply Voltage	Figure 10
Output Voltage Swing vs Output Current (Over Temperature)	Figure 11
Closed-Loop Gain vs Frequency, $G = 1, -1, 10$ (1.8 V)	Figure 12
Small-Signal Step Response, Noninverting (1.8 V)	Figure 13
Small-Signal Step Response, Noninverting (5.5 V)	Figure 14
Large-Signal Step Response, Noninverting (1.8 V)	Figure 15
Large-Signal Step Response, Noninverting (5.5 V)	Figure 16
No Phase Reversal	Figure 17
EMIRR IN+ vs Frequency	Figure 18

7.9 Typical Characteristics

at $T_A = 25^\circ\text{C}$, $V_S = 5\text{ V}$, $R_L = 10\text{ k}\Omega$ connected to $V_S / 2$, and $V_{CM} = V_{OUT} = V_S / 2$, (unless otherwise noted)

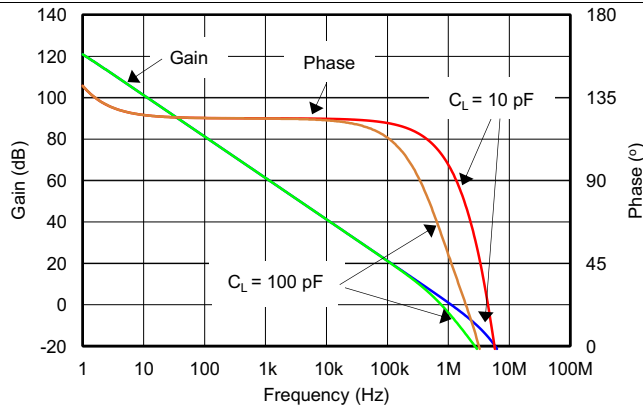


图 1. Open-Loop Gain and Phase vs Frequency

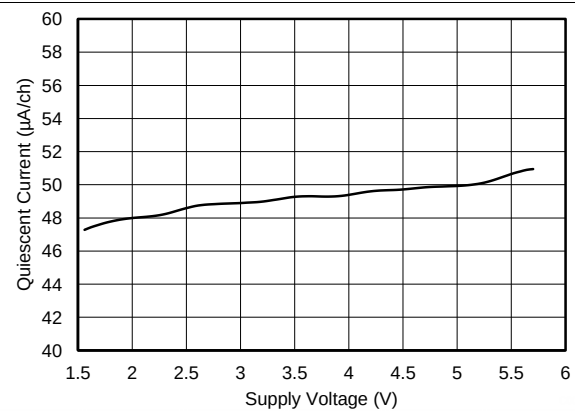


图 2. Quiescent Current vs Supply

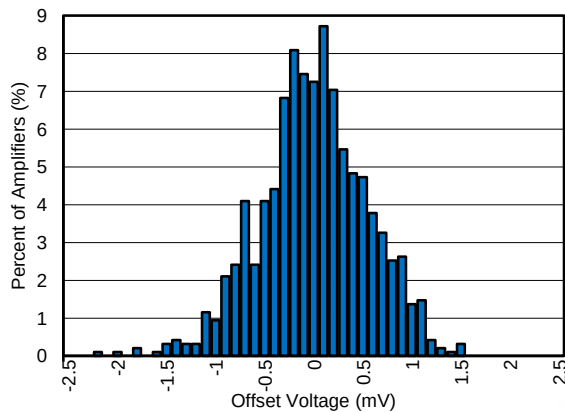


图 3. Offset Voltage Production Distribution

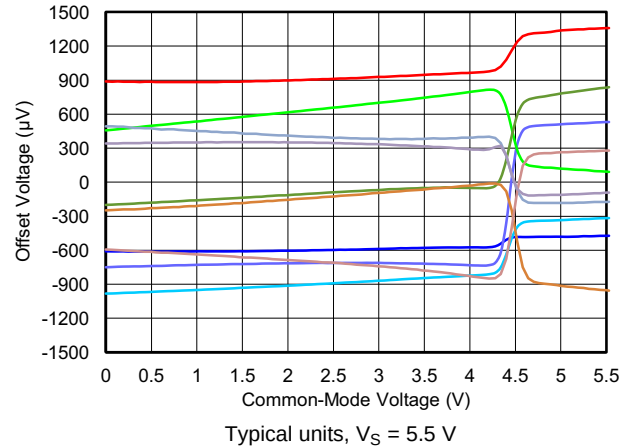


图 4. Offset Voltage vs Common-Mode Voltage

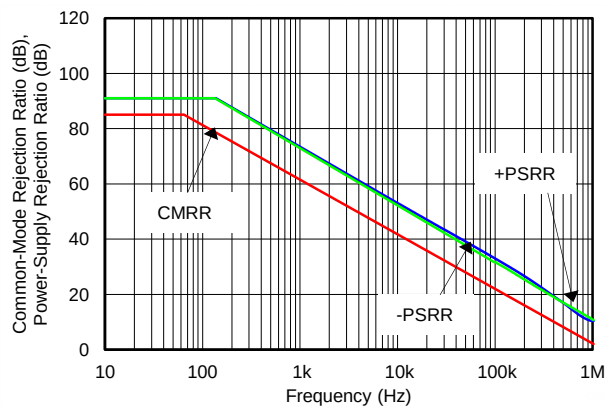


图 5. CMRR and PSRR vs Frequency
(Referred-to-Input)

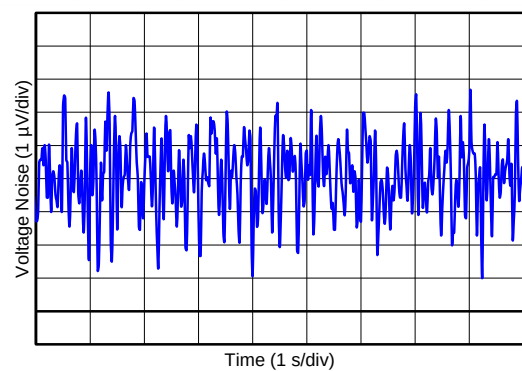


图 6. 0.1-Hz to 10-Hz Input Voltage Noise

Typical Characteristics (continued)

at $T_A = 25^\circ\text{C}$, $V_S = 5\text{ V}$, $R_L = 10\text{ k}\Omega$ connected to $V_S / 2$, and $V_{CM} = V_{OUT} = V_S / 2$, (unless otherwise noted)

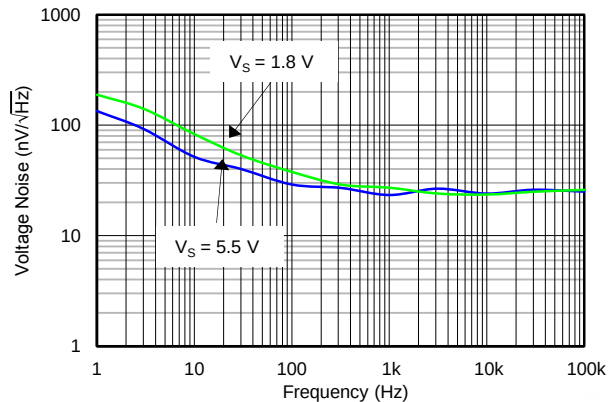


FIG 7. Input Voltage Noise Spectral Density vs Frequency

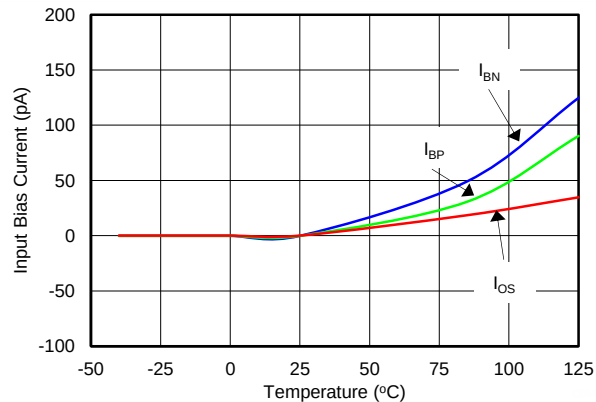


FIG 8. Input Bias and Offset Current vs Temperature

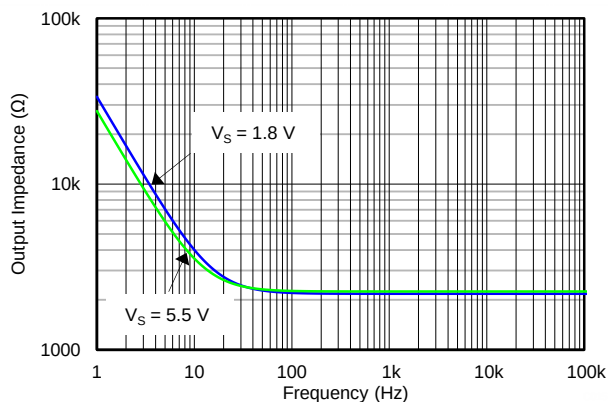
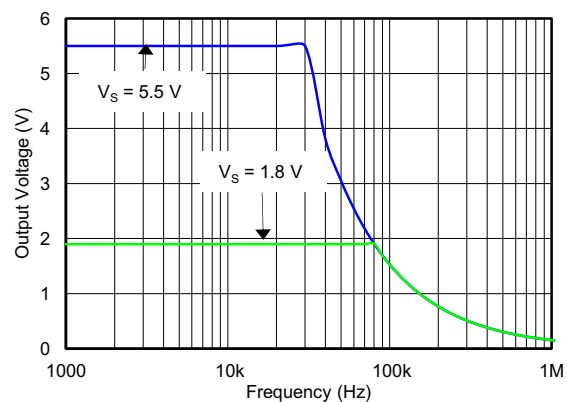


FIG 9. Open-Loop Output Impedance vs Frequency



$R_L = 10\text{ k}\Omega$

$C_L = 10\text{ pF}$

FIG 10. Maximum Output Voltage vs Frequency and Supply Voltage

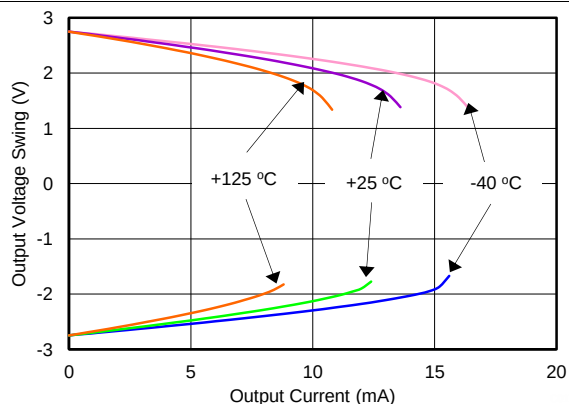


FIG 11. Output Voltage Swing vs Output Current (Over Temperature)

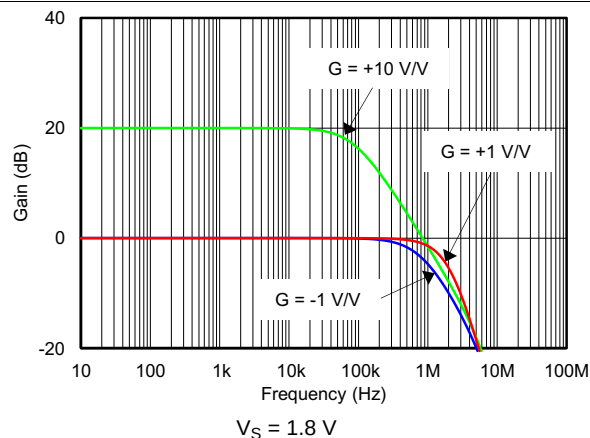


FIG 12. Closed-Loop Gain vs Frequency (Minimum Supply)

Typical Characteristics (continued)

at $T_A = 25^\circ\text{C}$, $V_S = 5\text{ V}$, $R_L = 10\text{ k}\Omega$ connected to $V_S / 2$, and $V_{CM} = V_{OUT} = V_S / 2$, (unless otherwise noted)

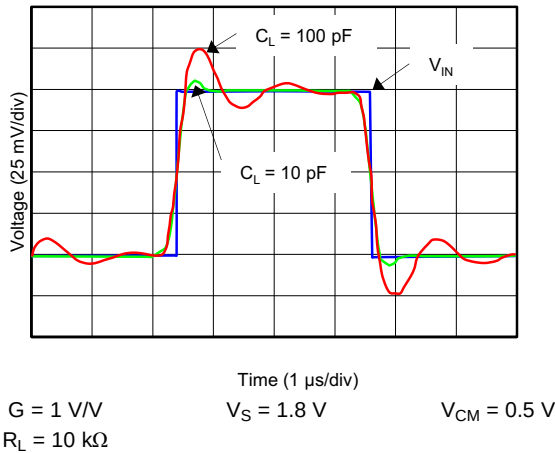


FIG 13. Small-Signal Pulse Response (Minimum Supply)

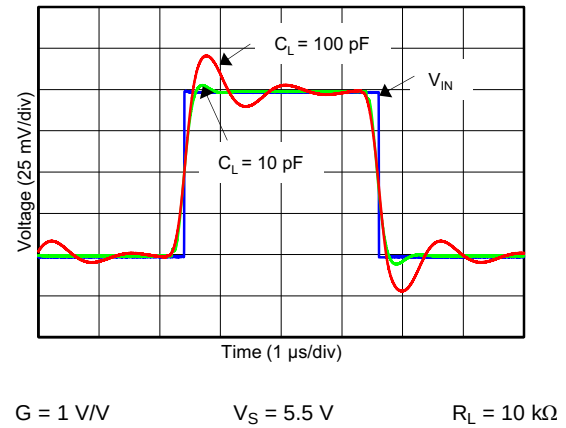


FIG 14. Small-Signal Pulse Response (Maximum Supply)

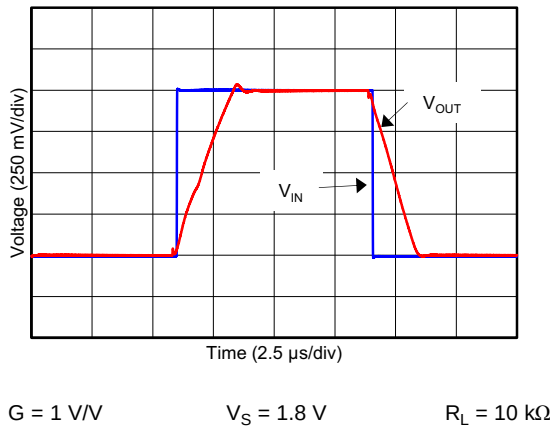


FIG 15. Large-Signal Pulse Response (Minimum Supply)

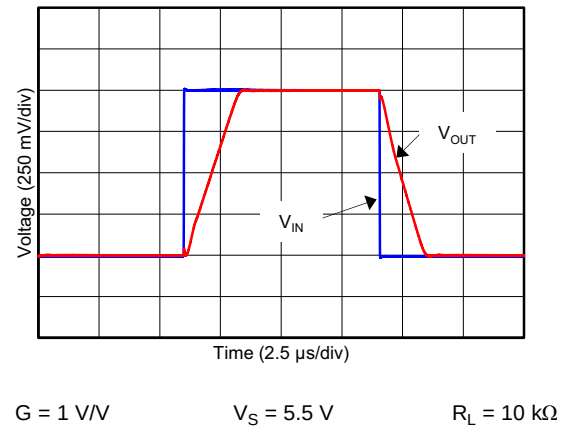


FIG 16. Large-Signal Pulse Response (Maximum Supply)

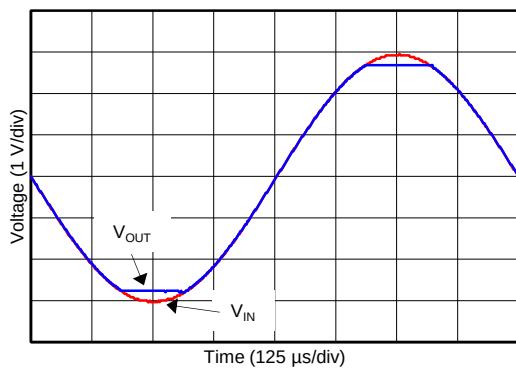


FIG 17. No Phase Reversal

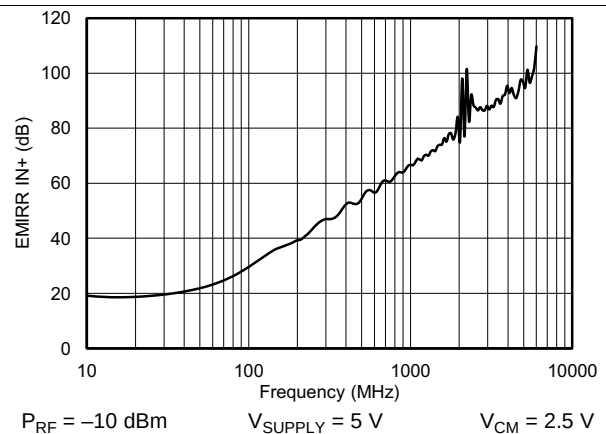


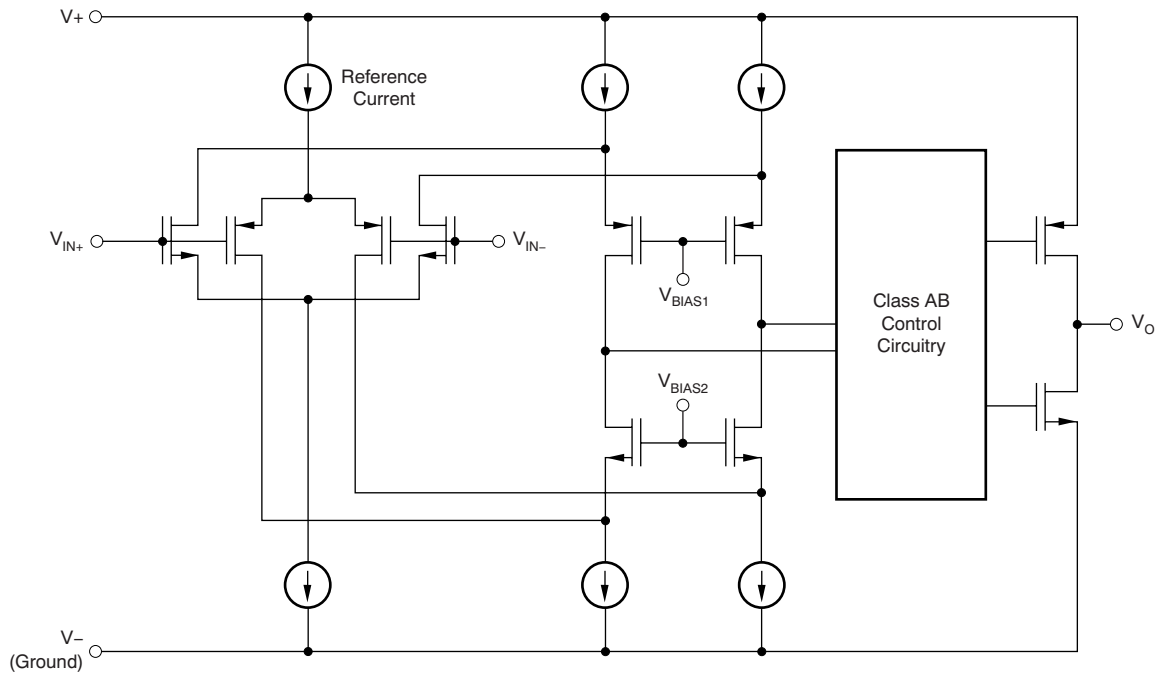
FIG 18. EMIRR IN+ vs Frequency

8 Detailed Description

8.1 Overview

The TLVx313-Q1 family of operational amplifiers are general-purpose devices that are designed for a wide range of portable, low-cost applications. Rail-to-rail input and output swings, low quiescent current, and wide dynamic range make the op amps designed for driving sampling analog-to-digital converters (ADCs) and other single-supply applications.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Operating Voltage

The TLVx313-Q1 family is fully specified and tested from 1.8 V to 5.5 V (± 0.9 V to ± 2.75 V). Parameters that vary with supply voltage are illustrated in the [Typical Characteristics](#) section.

8.3.2 Rail-to-Rail Input

The input common-mode voltage range of the TLVx313-Q1 family extends 200 mV beyond the supply rails. This performance is achieved with a complementary input stage: an N-channel input differential pair in parallel with a P-channel differential pair, as shown in the [Functional Block Diagram](#) section. The N-channel pair is active for input voltages close to the positive rail, typically $(V+) - 1.3$ V to 200 mV above the positive supply, while the P-channel pair is on for inputs from 200 mV below the negative supply to approximately $(V+) - 1.3$ V. There is a small transition region, typically $(V+) - 1.4$ V to $(V+) - 1.2$ V, in which both pairs are on. This 200-mV transition region may vary up to 300 mV with process variation. Thus, the transition region (both stages on) may range from $(V+) - 1.7$ V to $(V+) - 1.5$ V on the low end, up to $(V+) - 1.1$ V to $(V+) - 0.9$ V on the high end. Within this transition region, PSRR, CMRR, offset voltage, offset drift, and THD may be degraded compared to device operation outside this region.

8.3.3 Rail-to-Rail Output

Designed as a micro-power, low-noise operational amplifier, the TLVx313-Q1 family delivers a robust output drive capability. A class AB output stage with common-source transistors is used to achieve full rail-to-rail output swing capability. For resistive loads up to 100 k Ω , the output swings typically to within 5 mV of either supply rail regardless of the power-supply voltage applied. Different load conditions change the ability of the amplifier to swing close to the rails, as shown in [Figure 11](#).

8.3.4 Common-Mode Rejection Ratio (CMRR)

CMRR for the TLVx313-Q1 family is specified in several ways so the best match for a given application may be used; see the [Electrical Characteristics](#). First, the CMRR of the device in the common-mode range below the transition region ($V_{CM} < (V+) - 1.3$ V) is given. This specification is the best indicator of the capability of the device when the application requires use of one of the differential input pairs. Second, the CMRR over the entire common-mode range is specified at ($V_{CM} = -0.2$ V to 5.7 V). This last value includes the variations seen through the transition region, as shown in [Figure 4](#).

8.3.5 Capacitive Load and Stability

The TLVx313-Q1 family is designed to be used in applications where driving a capacitive load is required. As with all op amps, there may be specific instances where the TLVx313-Q1 device may become unstable. The particular op amp circuit configuration, layout, gain, and output loading are some of the factors to consider when establishing whether or not an amplifier is stable in operation. An op amp in the unity-gain ($+1$ -V/V) buffer configuration that drives a capacitive load exhibits a greater tendency to be unstable than an amplifier operated at a higher noise gain. The capacitive load, in conjunction with the op amp output resistance, creates a pole within the feedback loop that degrades the phase margin. The degradation of the phase margin increases as the capacitive loading increases. When operating in the unity-gain configuration, the TLVx313-Q1 device remains stable with a pure capacitive load up to approximately 1 nF. The equivalent series resistance (ESR) of some capacitors (C_L greater than 1 μ F) is sufficient to alter the phase characteristics in the feedback loop such that the amplifier remains stable. Increasing the amplifier closed-loop gain allows the amplifier to drive increasingly larger capacitance. This increased capability is evident when observing the overshoot response of the amplifier at higher voltage gains.

Feature Description (continued)

One technique for increasing the capacitive load drive capability of the amplifier when it operates in a unity-gain configuration is to insert a small resistor, typically $10\ \Omega$ to $20\ \Omega$, in series with the output, as shown in [Figure 19](#). This resistor significantly reduces the overshoot and ringing associated with large capacitive loads. One possible problem with this technique is that a voltage divider is created with the added series resistor and any resistor connected in parallel with the capacitive load. The voltage divider introduces a gain error at the output that reduces the output swing.

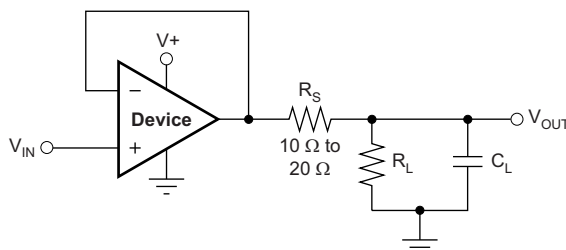


Figure 19. Improving Capacitive Load Drive

8.3.6 EMI Susceptibility and Input Filtering

Operational amplifiers vary with regard to the susceptibility of the device to electromagnetic interference (EMI). If conducted EMI enters the op amp, the DC offset observed at the amplifier output may shift from the nominal value while EMI is present. This shift is a result of signal rectification associated with the internal semiconductor junctions. While all op amp pin functions may be affected by EMI, the signal input pins are likely to be the most susceptible. The TLVx313-Q1 family incorporates an internal input low-pass filter that reduces the amplifiers response to EMI. Both common-mode and differential mode filtering are provided by this filter. The filter is designed for a common-mode cutoff frequency of approximately 35 MHz (–3 dB), with a rolloff of 20 dB per decade.

Texas Instruments has developed the ability to accurately measure and quantify the immunity of an operational amplifier over a broad frequency spectrum extending from 10 MHz to 6 GHz. The EMI rejection ratio (EMIRR) metric allows op amps to be directly compared by the EMI immunity. [Figure 18](#) illustrates the results of this testing on the TLV313-Q1 family. Detailed information may be found in [EMI Rejection Ratio of Operational Amplifiers](#), available for download from www.ti.com.

8.3.7 Input and ESD Protection

The TLVx313-Q1 family incorporates internal electrostatic discharge (ESD) protection circuits on all pins. In the case of input and output pins, this protection primarily consists of current-steering diodes connected between the input and power-supply pins. The ESD protection diodes also provide in-circuit, input overdrive protection, as long as the current is limited to 10 mA as stated in the [Absolute Maximum Ratings](#). [Figure 20](#) shows how a series input resistor may be added to the driven input to limit the input current. The added resistor contributes thermal noise at the amplifier input and the value must be kept to a minimum in noise-sensitive applications.

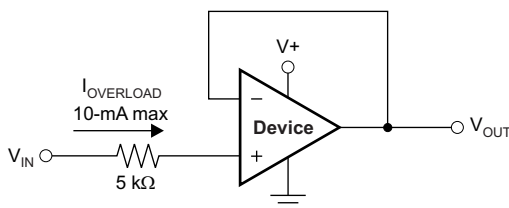


Figure 20. Input Current Protection

8.4 Device Functional Modes

The TLV313-Q1 devices have a single functional mode. The devices are powered on as long as the power-supply voltage is between 1.8 V (± 0.9 V) and 5.5 V (± 2.75 V).

9 Application and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The TLVx313-Q1 devices are a family of low-power, rail-to-rail input and output operational amplifiers specifically designed for portable applications. The devices operate from 1.8 V to 5.5 V, are unity-gain stable, and are designed for a wide range of general-purpose applications. The class AB output stage is capable of driving loads greater than 10 kΩ connected to any point between V₊ and ground. The input common-mode voltage range includes both rails, and allows the TLVx313-Q1 family to be used in virtually any single-supply application.

9.2 Typical Application

A typical application for an operational amplifier is an inverting amplifier, as shown in [Figure 21](#). An inverting amplifier takes a positive voltage on the input and outputs a signal inverted to the input, making a negative voltage of the same magnitude. In the same manner, the amplifier also makes negative input voltages positive on the output. In addition, amplification may be added by selecting the input resistor (R_I) and the feedback resistor (R_F).

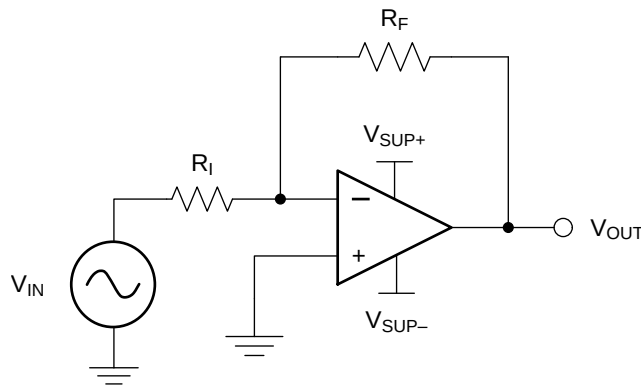


Figure 21. Application Schematic

9.2.1 Design Requirements

The supply voltage must be chosen to be larger than the input voltage range and the desired output range. The limits of the input common-mode range (V_{CM}) and the output voltage swing to the rails (V_O) must also be considered. For instance, this application scales a signal of ±0.5 V (1 V) to ±1.8 V (3.6 V). Setting the supply at ±2.5 V is sufficient to accommodate this application.

9.2.2 Detailed Design Procedure

Determine the gain required by the inverting amplifier using [Equation 1](#) and [Equation 2](#):

$$A_V = \frac{V_{OUT}}{V_{IN}} \quad (1)$$

$$A_V = \frac{1.8}{-0.5} = -3.6 \quad (2)$$

Typical Application (continued)

When the desired gain is determined, choose a value for R_I or R_F . Choosing a value in the kilohm range is desirable for general-purpose applications because the amplifier circuit uses currents in the milliamp range. This milliamp current range ensures the device does not draw too much current. The trade-off is that very large resistors (100s of kilohms) draw the smallest current but generate the highest noise. Small resistors (100s of ohms) generate low noise but draw high current. This example uses 10 k Ω for R_I , meaning 36 k Ω is used for R_F . The values are determined by 式 3:

$$A_V = -\frac{R_F}{R_I} \quad (3)$$

9.2.3 Application Curve

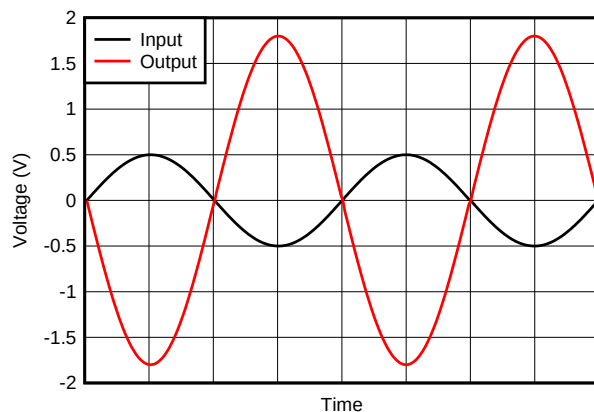
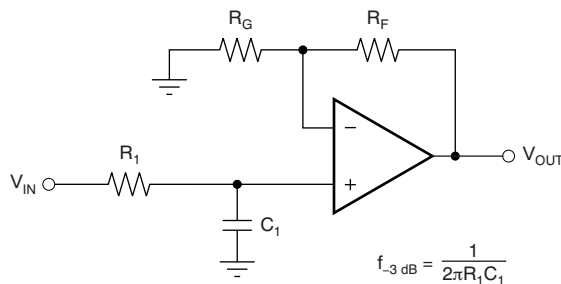


图 22. Inverting Amplifier Input and Output

9.3 System Examples

When receiving low-level signals, limiting the bandwidth of the incoming signals into the system is often required. The simplest way to establish this limited bandwidth is to place an RC filter at the noninverting terminal of the amplifier, as shown in 图 23.



$$\frac{V_{OUT}}{V_{IN}} = \left(1 + \frac{R_F}{R_G}\right) \left(\frac{1}{1 + sR_I C_1}\right)$$

图 23. Single-Pole Low-Pass Filter

System Examples (continued)

If even more attenuation is needed, a multiple pole filter is required. The Sallen-Key filter may be used for this task, as shown in [Figure 24](#). For best results, the amplifier must have a bandwidth that is eight to 10 times the filter frequency bandwidth. Failure to follow this guideline may result in phase shift of the amplifier.

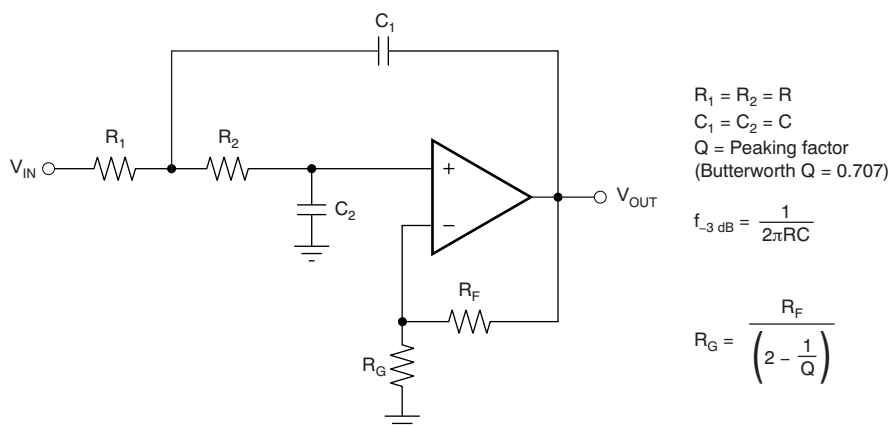


Figure 24. Two-Pole, Low-Pass, Sallen-Key Filter

10 Power Supply Recommendations

The TLVx313-Q1 family is specified for operation from 1.8 V to 5.5 V (± 0.9 V to ± 2.75 V); many specifications apply from -40°C to $+125^\circ\text{C}$. The [Typical Characteristics](#) section presents parameters that may exhibit significant variance with regard to operating voltage or temperature.

注意

Supply voltages larger than 7 V can permanently damage the device (see the [Absolute Maximum Ratings](#) table).

Place 0.1- μF bypass capacitors close to the power-supply pins to reduce errors coupling in from noisy or high-impedance power supplies. For more detailed information on bypass capacitor placement, refer to the [Layout Guidelines](#) section.

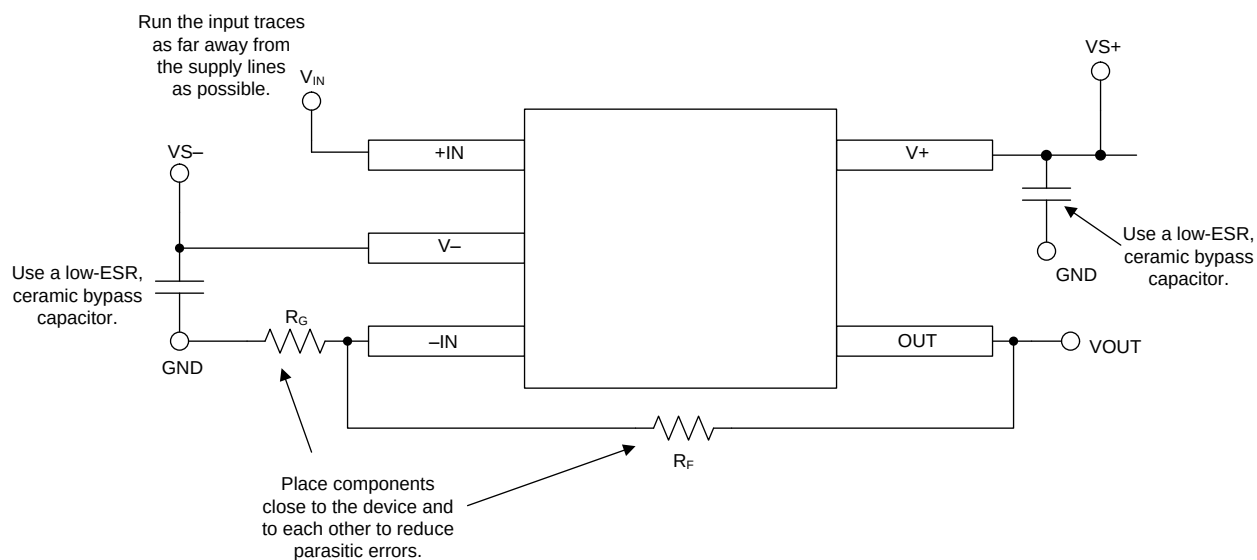
11 Layout

11.1 Layout Guidelines

For best operational performance of the device, use good printed circuit board (PCB) layout practices, including:

- Noise may propagate into analog circuitry through the power pins of the circuit and the operational amplifier. Use bypass capacitors to reduce the coupled noise by providing low-impedance power sources local to the analog circuitry.
 - Connect low-ESR, 0.1- μ F ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is applicable for single-supply applications.
- Separate grounding for analog and digital portions of the circuitry is one of the simplest and most effective methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to ground planes. A ground plane helps distribute heat and reduces EMI noise pickup. Take care to physically separate digital and analog grounds, paying attention to the flow of the ground current. For more detailed information, see [Circuit Board Layout Techniques](#).
- To reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If the traces cannot be kept separate, crossing the sensitive trace perpendicularly is much better than crossing in parallel with the noisy trace.
- Place the external components as close to the device as possible. Keep R_F and R_G close to the inverting input to minimize parasitic capacitance, as shown in [Figure 25](#).
- Keep the length of input traces as short as possible. Remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring may significantly reduce leakage currents from nearby traces that are at different potentials.

11.2 Layout Example: Single Channel



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Figure 25. Operational Amplifier Board Layout for Noninverting Configuration

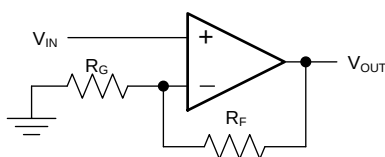
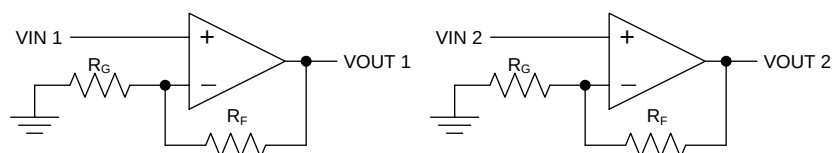
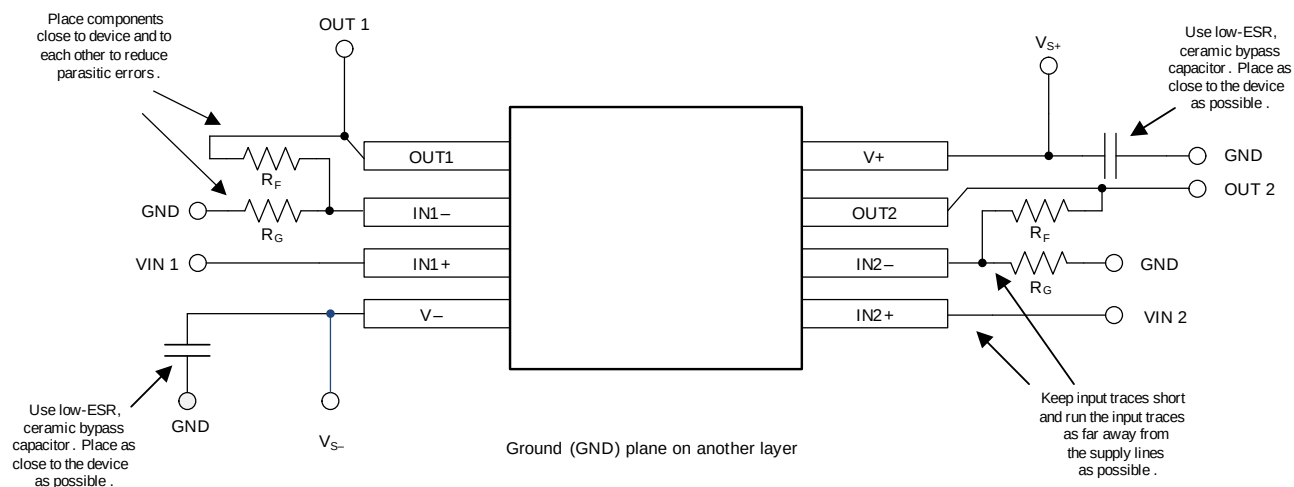


Figure 26. Schematic Representation of Figure 25

11.3 Layout Example: Dual Channel



⊗ 27. Schematic Representation for ⊗ 28



⊗ 28. Layout Example

12 デバイスおよびドキュメントのサポート

12.1 ドキュメントのサポート

12.1.1 関連資料

関連資料については、以下を参照してください。

- 『[オペアンプのEMI除去率](#)』
- 『[基板のレイアウト技法](#)』

12.2 関連リンク

次の表に、クイック・アクセス・リンクを示します。カテゴリには、技術資料、サポートおよびコミュニティ・リソース、ツールとソフトウェア、およびご注文へのクイック・アクセスが含まれます。

表 2. 関連リンク

製品	プロダクト・フォルダ	ご注文はこちら	技術資料	ツールとソフトウェア	サポートとコミュニティ
TLV313-Q1	ここをクリック	ここをクリック	ここをクリック	ここをクリック	ここをクリック
TLV2313-Q1	ここをクリック	ここをクリック	ここをクリック	ここをクリック	ここをクリック

12.3 ドキュメントの更新通知を受け取る方法

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12.4 コミュニティ・リソース

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

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12.5 商標

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12.6 静電気放電に関する注意事項



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静電気放電はわずかな性能の低下から完全なデバイスの故障に至るまで、様々な損傷を与えます。高精度の集積回路は、損傷に対して敏感であり、極めてわずかなパラメータの変化により、デバイスに規定された仕様に適合しなくなる場合があります。

12.7 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 メカニカル、パッケージ、および注文情報

以降のページには、メカニカル、パッケージ、および注文に関する情報が記載されています。この情報は、そのデバイスについて利用可能な最新のデータです。このデータは予告なく変更されることがあり、ドキュメントが改訂される場合もあります。本データシートのブラウザ版を使用されている場合は、画面左側の説明をご覧ください。

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
TLV2313QDGKRQ1	Active	Production	VSSOP (DGK) 8	2500 LARGE T&R	Yes	NIPDAU NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	1NJ6
TLV2313QDGKRQ1.B	Active	Production	VSSOP (DGK) 8	2500 LARGE T&R	Yes	NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	1NJ6
TLV2313QDRQ1	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	V2313Q
TLV2313QDRQ1.B	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	V2313Q
TLV313QDCKRQ1	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	NIPDAUAG SN	Level-1-260C-UNLIM	-40 to 125	19A
TLV313QDCKRQ1.B	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	19A
TLV313QDCKTQ1	Active	Production	SC70 (DCK) 5	250 SMALL T&R	Yes	NIPDAUAG SN	Level-1-260C-UNLIM	-40 to 125	19A
TLV313QDCKTQ1.B	Active	Production	SC70 (DCK) 5	250 SMALL T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	19A

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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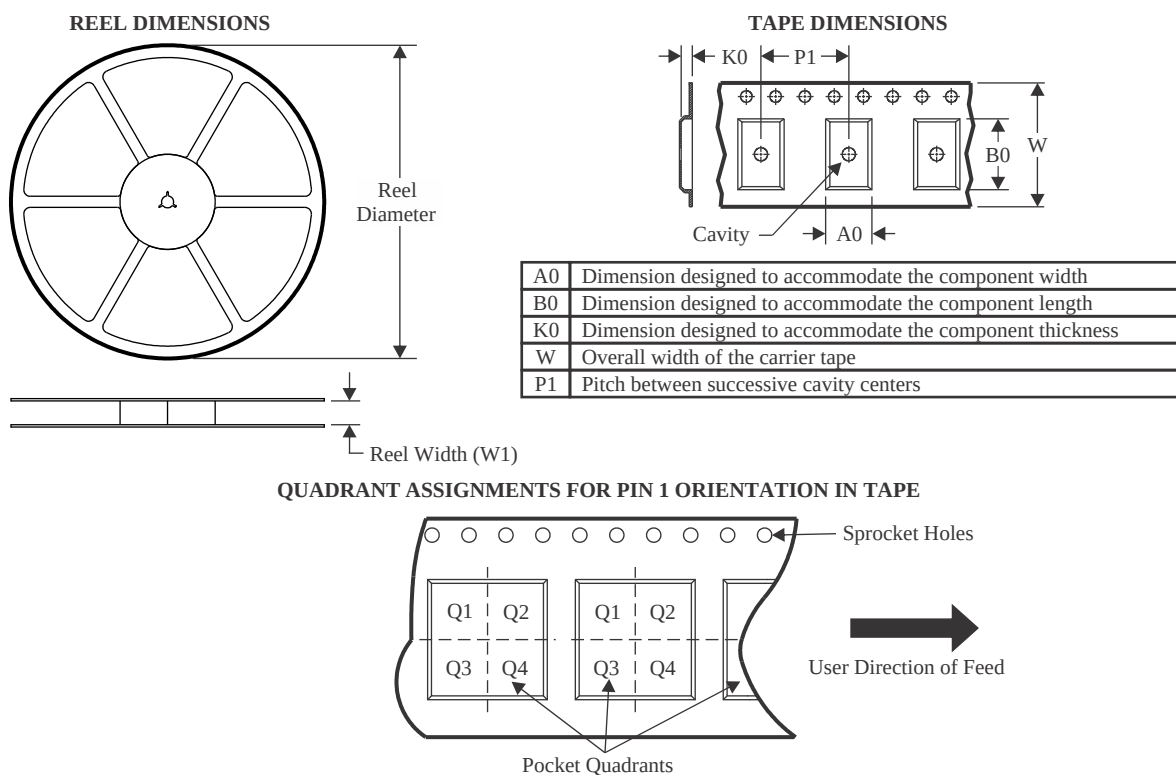
OTHER QUALIFIED VERSIONS OF TLV2313-Q1, TLV313-Q1 :

- Catalog : [TLV2313](#), [TLV313](#)

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product

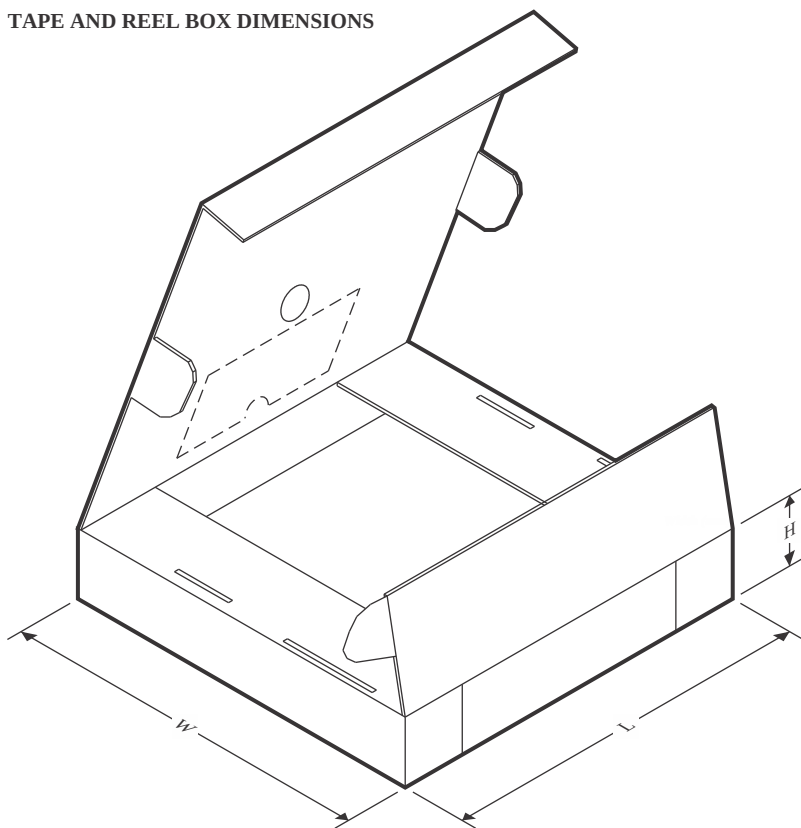
TAPE AND REEL INFORMATION



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV2313QDGKRQ1	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TLV2313QDRQ1	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLV313QDCKRQ1	SC70	DCK	5	3000	180.0	8.4	2.47	2.3	1.25	4.0	8.0	Q3
TLV313QDCKTQ1	SC70	DCK	5	250	180.0	8.4	2.3	2.55	1.2	4.0	8.0	Q3
TLV313QDCKTQ1	SC70	DCK	5	250	180.0	8.4	2.47	2.3	1.25	4.0	8.0	Q3

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV2313QDGKRQ1	VSSOP	DGK	8	2500	353.0	353.0	32.0
TLV2313QDRQ1	SOIC	D	8	2500	353.0	353.0	32.0
TLV313QDCKRQ1	SC70	DCK	5	3000	183.0	183.0	20.0
TLV313QDCKTQ1	SC70	DCK	5	250	210.0	185.0	35.0
TLV313QDCKTQ1	SC70	DCK	5	250	183.0	183.0	20.0

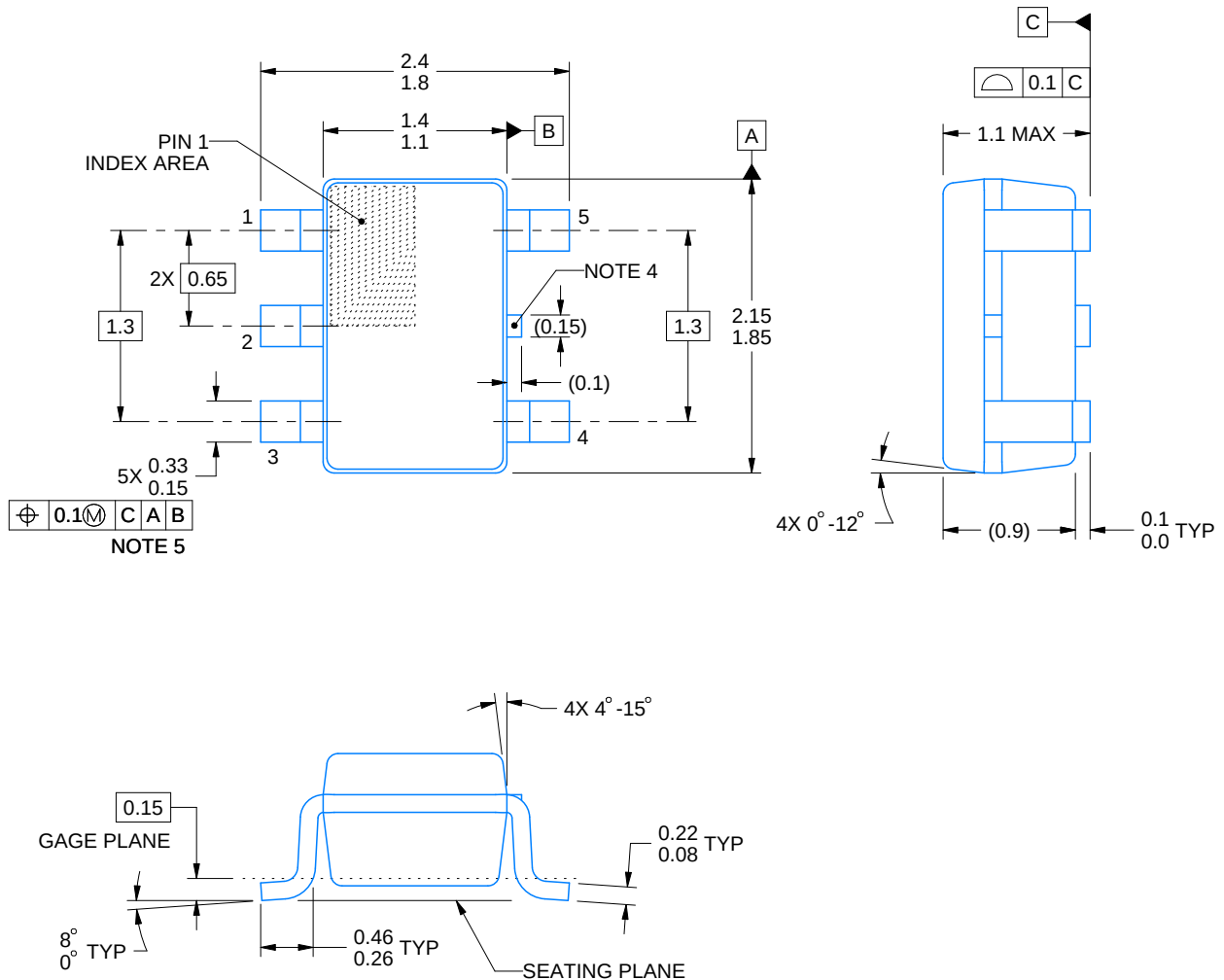
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PACKAGE OUTLINE

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



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NOTES:

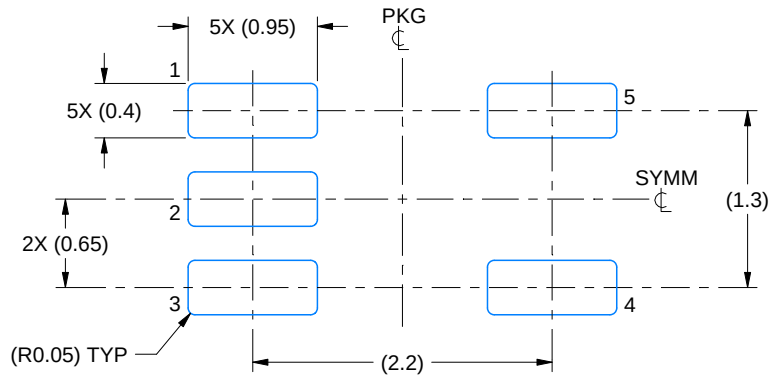
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Reference JEDEC MO-203.
4. Support pin may differ or may not be present.
5. Lead width does not comply with JEDEC.
6. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25mm per side

EXAMPLE BOARD LAYOUT

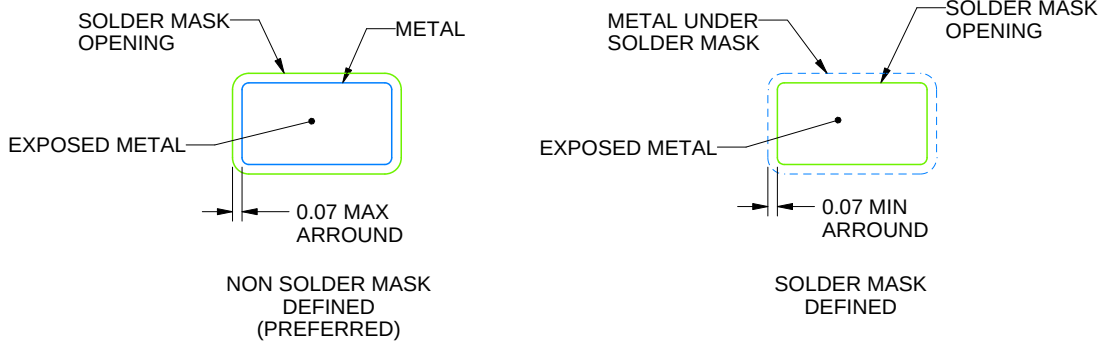
DCK0005A

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:18X



SOLDER MASK DETAILS

4214834/G 11/2024

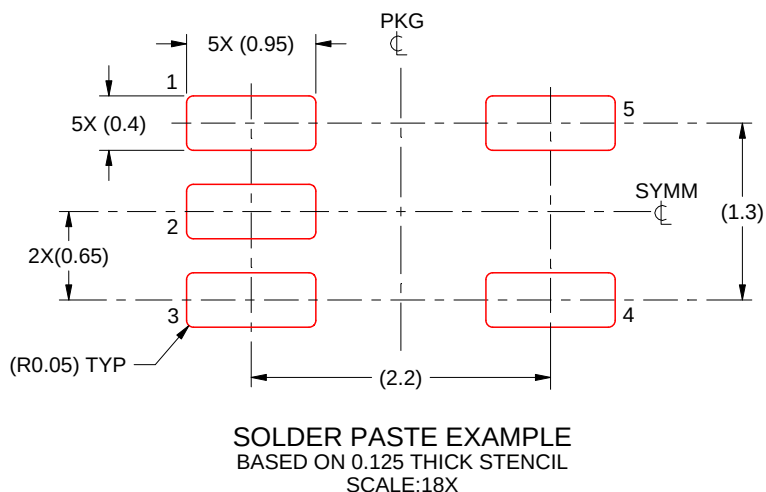
NOTES: (continued)

7. Publication IPC-7351 may have alternate designs.
8. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

DCK0005A

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



4214834/G 11/2024

NOTES: (continued)

9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
10. Board assembly site may have different recommendations for stencil design.



PACKAGE OUTLINE

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



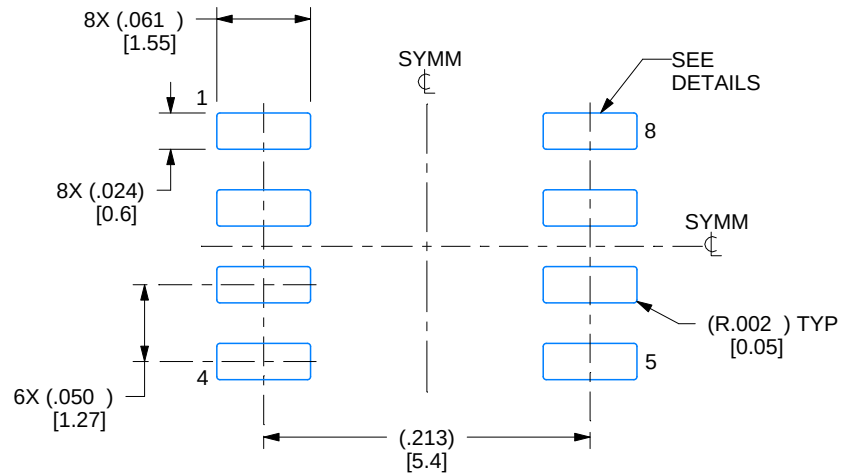
1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MS-012, variation AA.

EXAMPLE BOARD LAYOUT

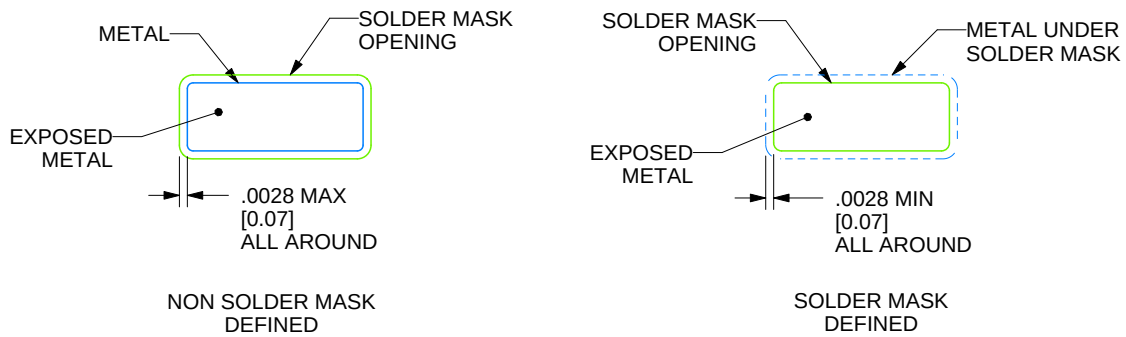
D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:8X



SOLDER MASK DETAILS

4214825/C 02/2019

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

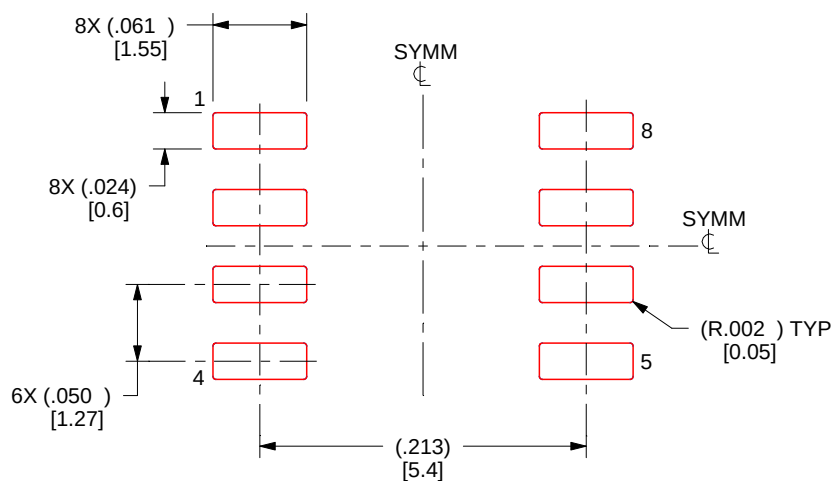
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



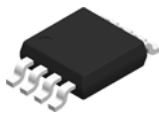
SOLDER PASTE EXAMPLE
BASED ON .005 INCH [0.125 MM] THICK STENCIL
SCALE:8X

4214825/C 02/2019

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

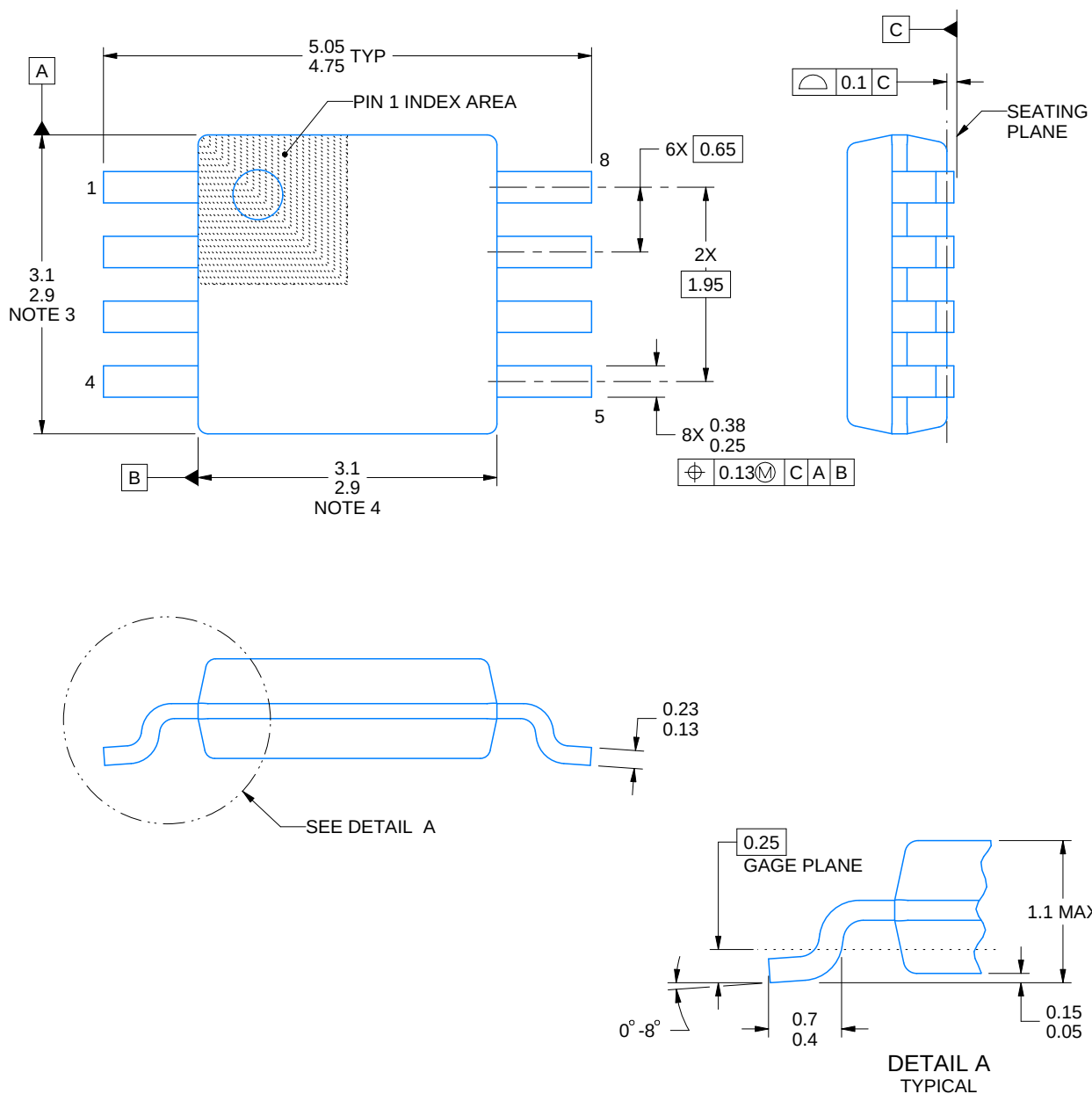
DGK0008A



PACKAGE OUTLINE

VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



4214862/A 04/2023

NOTES:

PowerPAD is a trademark of Texas Instruments.

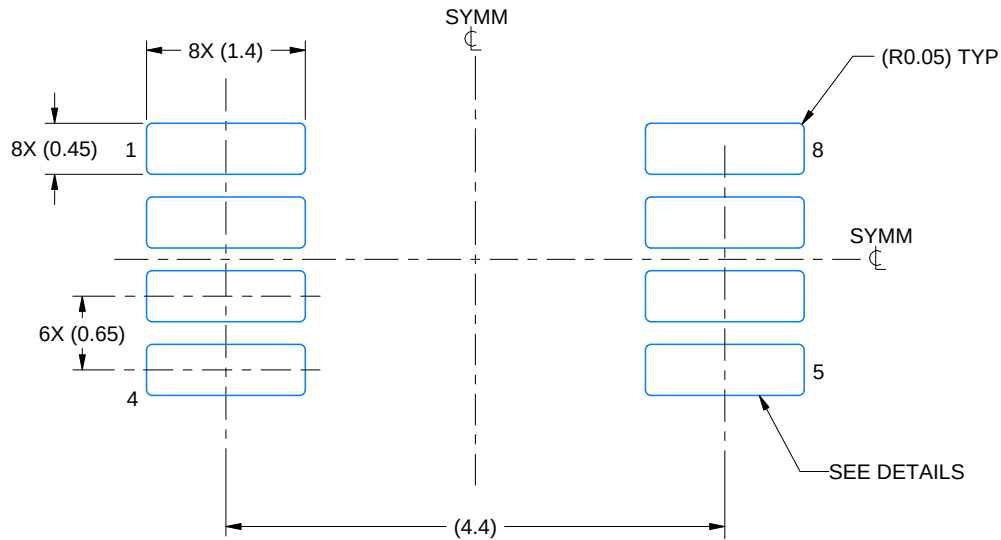
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-187.

EXAMPLE BOARD LAYOUT

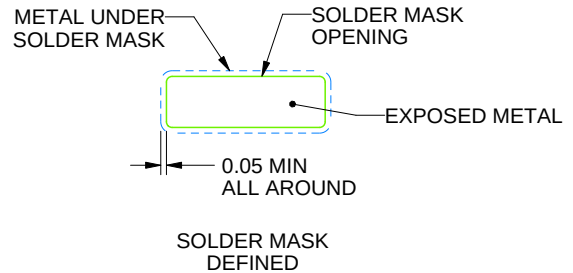
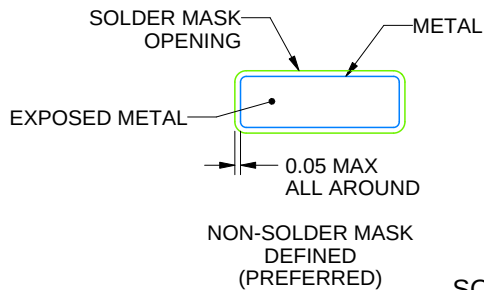
DGK0008A

TM VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 15X



SOLDER MASK DETAILS

4214862/A 04/2023

NOTES: (continued)

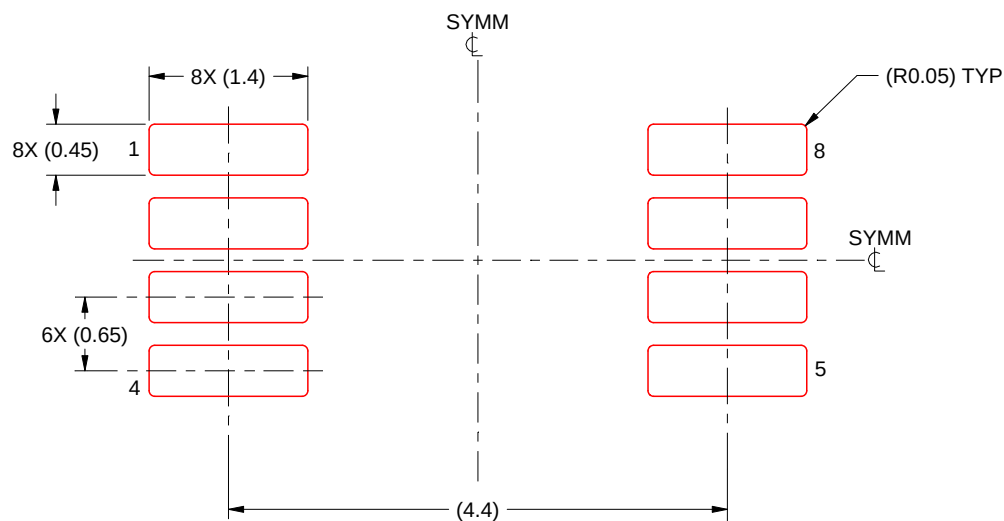
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
8. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.
9. Size of metal pad may vary due to creepage requirement.

EXAMPLE STENCIL DESIGN

DGK0008A

™ VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
SCALE: 15X

4214862/A 04/2023

NOTES: (continued)

11. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
12. Board assembly site may have different recommendations for stencil design.

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